MS TF1110





Key Parameters

Vdrm / Vrrm	= 2000V
IT(AV)	= 1110A
Тѕм	= 19.2kA
V _{T(TO)}	= 1.207V
rт	= 0.342mΩ

Features

- Full blocking capability over wide temperature range
- High Surge current capability .
- Hermetic metal case with ceramic insulator .
- Distributed gate

- ApplicationsBattery Chargers
- Medical Equipment
- . UPS
- . Power Supplies
- . Motor control
- Transportation
- Induction Heating -
- Welding

Ordering Information

MS TF	1110	С	XX	Н	2J
Fast Switching Thyristor	Current Code	C - Capsule package with Alloyed silicon technology	Voltage Code Code X 100 = V _{DRM} /V _{RRM}	Reapplied dv/dt H =400V/µsec	Turn Off time code 2J = 50µsec 4J = 100µsec
Order Code MS	TF1110C2	20H2J – 2000V V _{DRM} , V _{RRM} , T _q =	50µsec, 26mm clamp heig	ht capsule	
			Prepared by : ABA	Date of Publication	: 25.03.2015
			Approved by : RBS	Revision	: 0

Technical Information Fast Switching Thyristor

MS TF1110

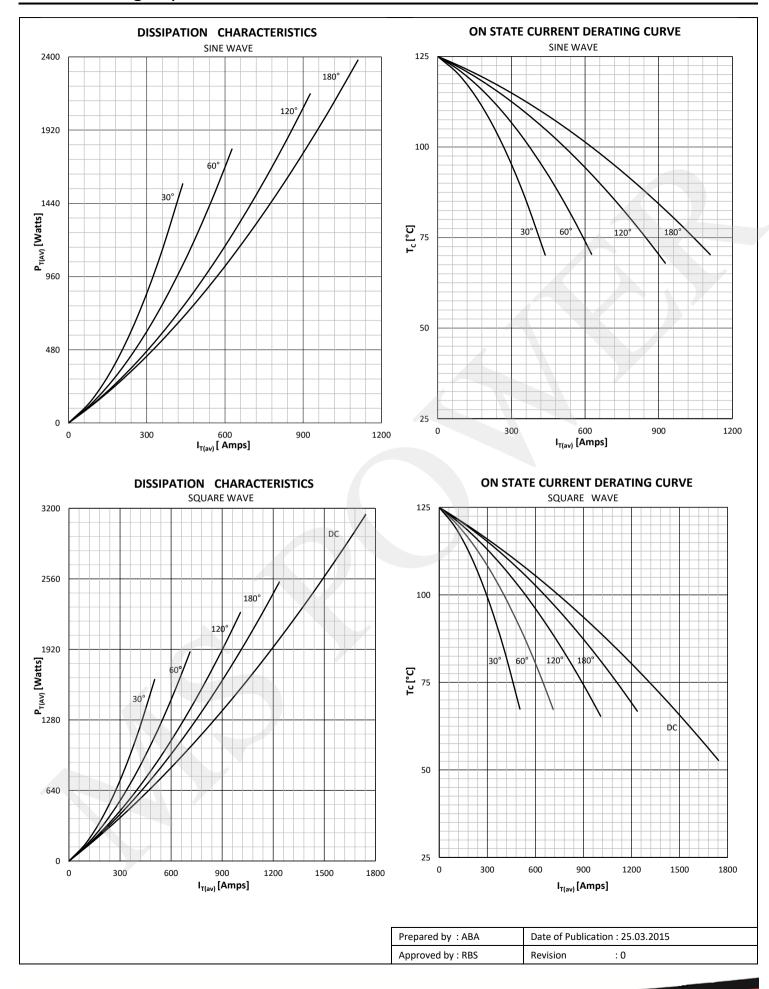


Symbol	Characteristic	Conditions	Tj [°C]	Value	Unit
BLOCKI	NG				
V RRM	Repetitive peak reverse voltage		125	1400 - 2000	V
V RSM	Non-repetitive peak reverse voltage		125	1500 - 2100	V
V drm	Repetitive peak off-state voltage		125	1400 - 2000	V
I RRM	Repetitive peak reverse current	V= V RRM	125	90	mA
DRM	Repetitive peak off-state current	V= V drm	125	90	mA
CONDU	CTING				
I T (AV)	Mean on state current	180° sin ,50 Hz, T_c =70°C, Double side cooled 180° sin ,50 Hz, T_c =77°C, Double side cooled		1110 1000	A
I RMS	RMS on-state current	T _c =70°C, Double side cooled		1743	А
1		Sine wave, 10 ms	25	19200	Α
I TSM	Surge on-state current	Without reverse voltage	125	18500	Α
		Sine wave, 10 ms	25	1843 x 10 ³	A ² s
l² t	l ² t	Without reverse voltage	125	1711 x 10 ³	A²s
νт	On-state voltage	On-state current = 2000A	125	1.90	V
V T(TO)	Threshold voltage		125	1.207	V
rт	On-state slope resistance		125	0.342	mΩ
SWITCH	ING				
di/dt	Critical rate of rise of on-state current	Repetitive	125	250	A/µs
dv/dt	Critical rate of rise of off-state voltage	$V_{DR} = 67\% V_{DRM}$	125	400	V/µs
Τq	Circuit commutated turn off time	I _{TM} =1000A, -di _F /dt = 60A/μs, V _R = 100V,t _p =1000μs Reapplied dv/dt = 400V/μs, V _{DR} = 80%V _{DRM}	125	50 - 100	μs
GATE	1				
l _{gt}	Gate trigger current	V _D =6V	25	200	mA
V _{gt}	Gate trigger voltage	V _D =6V	25	3.0	V
Iн	Holding current	V _D =6V, gate open circuit	25	600	mA
I L	Latching current	V _D =6V	25	1000	mA
MOUNT	NG		I		
R th(j-c)	Thermal impedance, sin 180°	Junction to case, Double side cooled		0.023	°C/W
R th(j-c)	Thermal impedance, rec120°	Junction to case, Double side cooled		0.026	°C/W
R th(c-h)	Thermal impedance	Case to heatsink, Double side cooled		0.0075	°C/W
Тj	Max. junction temperature			125	°C
T stg	Storage temperature			-40 125	°C
М	Clamping Force			22 - 24	kN
	Weight (Approx.)			500	gm

Prepared by : ABA	Date of Publication : 25.03.2015
Approved by : RBS	Revision : 0

MS TF1110

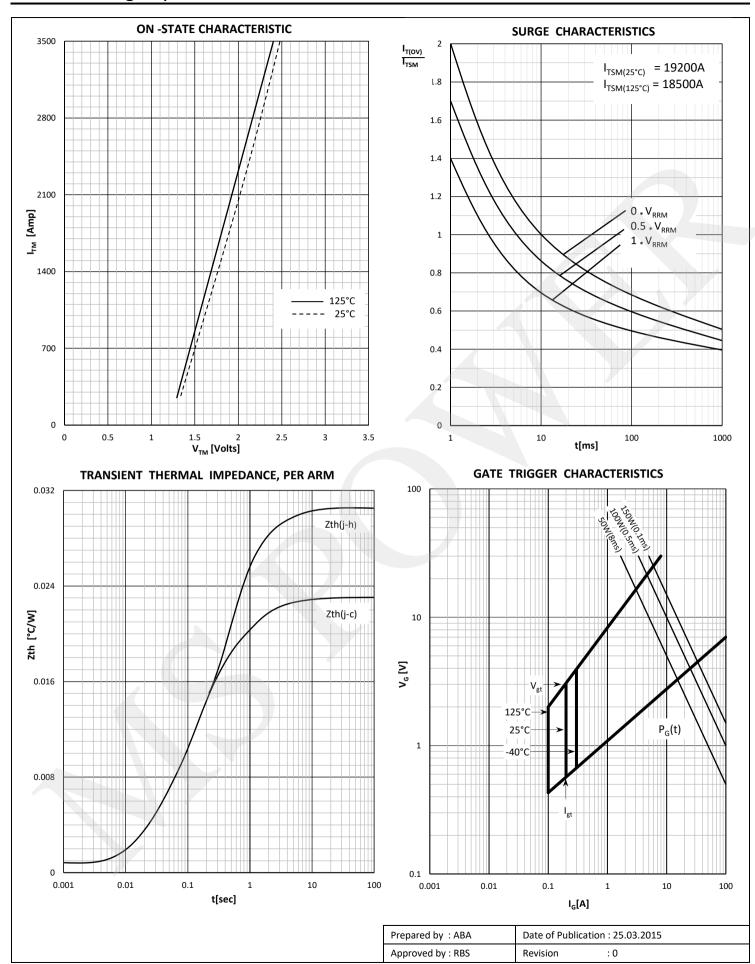




Technical Information Fast Switching Thyristor

MS TF1110

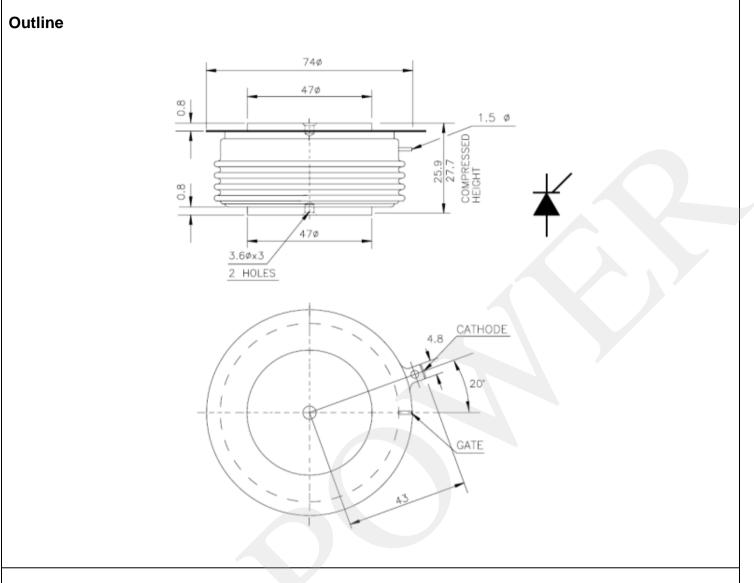




Technical Information Fast Switching Thyristor

MS TF1110





MS Power GmbH

Mergenthalerallee 79-81 65760 Eschborn, Germany Web: www.mspowergroup.com Mail: info@mspowergroup.de

Sales & Enquiry:

sales@mspowergroup.de Technical Support: solution@mspowergroup.de After sales Service: service@mspowergroup.de

Phone: +49 (0) 6196/7768 666 Fax: +49 (0) 6196/7757 888



 Prepared by : ABA
 Date of Publication : 25.03.2015

 Approved by : RBS
 Revision : 0

MS TF1110



Terms & Conditions of usage :

The data contained in this product datasheet is exclusively Intended for technically trained staff. You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application. This product datasheet is describing the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its characteristics. The information in the valid application-and assembly notes of the device must be considered.

Should you require product information in excess of the data given in this product datasheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you (see <u>www.mspowergroup.com</u>). For those that are specifically interested we may provide application notes.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the Product in aviation applications, in health or live endangering or life support applications, please notify. Please note, that for any such applications we urgently recommend

-to perform joint Risk and Quality Assessments;

-the conclusion of Quality Agreements;

-to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

If and to the extent necessary, please forward equivalent notices to your customers.

Changes of this product datasheet are reserved.

.5	: 25.03.2015	15	;															;	;	5	5	5	5	;	;	,								;	;	;	5	5	5	5	1	11):	С	.0	2	2	.2					3.	3.	3	3	3	3	3	3	3	3	0	.(;.	5.	5.	5		2!	2	2	2	2	;	: :	:	:	:	:		ı	n	5	ic	ıt	27	ic	li	b	u	יו	P	ſ	f	of	of	0	<u>.</u> (e	ιe	t	a	ז	0	ſ																																
	: 0																																																																				1))	D	0	С	(. (:	:	:	:	:												1	n	m	or	io	ic	si	is	/i:	v	e١	26	F																																	
				 	 -	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-		-	-	-	-	-	-	-	-	-